L Number	Hits	Search Text	DB	Time stamp
1	1021	438/424.ccls.	USPAT	2004/10/20
				19:11
2	347	438/427.ccls.	USPAT	2004/10/20
				19:11
3	169	438/453.ccls.	USPAT	2004/10/20
]			19:11
4	757	438/618.ccls.	USPAT	2004/10/20
				19:12
5	1102	438/622.ccis.	USPAT	2004/10/20
_				19:12
6	279	438/636.ccls.	USPAT	2004/10/20
_	4==0	400,000		19:12
7	1576	438/637.ccls.	USPAT	2004/10/20
•	132	438/444.ccis.	HODAT	19:12
8	132	438/444.CCIS.	USPAT	2004/10/20
9	723	438/700.ccls.	USPAT	19:12 2004/10/20
3	/23	430// 00.ccis.	USPAI	19:12
10	770	438/710.ccls.	USPAT	2004/10/20
	''	430/1 10:0013:	OSFAI	19:12
11	610	438/725.ccls.	USPAT	2004/10/20
			John	19:13
12	189	deloach-juanita\$.in. smith-brian\$.in.	USPAT	2004/10/20
		• • • • • • • • • • • • • • • • • • • •		19:14
13	76	deloach-juanita\$.in. smith-brian\$.in.	US-PGPUB	2004/10/20
				19:13
14	143	deloach-juanita\$.in. smith-brian\$.in.	EPO; JPO;	2004/10/20
			DERWENT;	19:13
			IBM_TDB	
15	90263	(trench open\$6 groov\$6 recess\$6) and	USPAT	2004/10/20
		plasma		19:19
16	28121	((trench open\$6 groov\$6 recess\$6) and	USPAT	2004/10/20
		plasma) and (resist photoresist)		19:16
17	13154	(((trench open\$6 groov\$6 recess\$6) and	USPAT	2004/10/20
		plasma) and (resist photoresist)) and		19:17
		((resist photoresist) same plasma)		
18	892	((((trench open\$6 groov\$6 recess\$6) and	USPAT	2004/10/20
		plasma) and (resist photoresist)) and		19:20
		((resist photoresist) same plasma)) and		
19	711	((resist photoresist) adj2 plasma)	HODAT	0004/40/00
13	/11	(((((trench open\$6 groov\$6 recess\$6) and	USPAT	2004/10/20
		plasma) and (resist photoresist)) and (resist photoresist) same plasma)) and		19:21
		((resist photoresist) same plasma)) and ((resist photoresist) adj2 plasma)) and		
		(isolat\$9 transistor interconnect\$6)		
21	13573	(trench open\$6 groov\$6 recess\$6) and	US-PGPUB	2004/10/20
		plasma and (resist photoresist)	JU-FUE	19:20
23	294	((trench open\$6 groov\$6 recess\$6) and	US-PGPUB	2004/10/20
		plasma and (resist photoresist)) and ((resist	33.3.35	19:20
		photoresist) adj2 plasma)		

24	2160	(trench open\$6 groov\$6 recess\$6) and	EPO; JPO;	2004/10/20
		plasma and (resist photoresist)	DERWENT;	19:20
			IBM_TDB	
25	84	((trench open\$6 groov\$6 recess\$6) and	EPO; JPO;	2004/10/20
		plasma and (resist photoresist)) and ((resist	DERWENT;	19:20
		photoresist) adj2 plasma)	IBM_TDB	
26	70	(((trench open\$6 groov\$6 recess\$6) and	EPO; JPO;	2004/10/20
		plasma and (resist photoresist)) and ((resist	DERWENT;	19:21
		photoresist) adj2 plasma)) and ((trench	IBM_TDB	
		open\$6 groov\$6 recess\$6) same plasma)		
27	1793	((trench open\$6 groov\$6 recess\$6) and	EPO; JPO;	2004/10/20
		plasma and (resist photoresist)) and	DERWENT;	19:21
		((trench open\$6 groov\$6 recess\$6) same	IBM_TDB	
		plasma)		
28	442	(((trench open\$6 groov\$6 recess\$6) and	EPO; JPO;	2004/10/20
		plasma and (resist photoresist)) and	DERWENT;	19:21
		((trench open\$6 groov\$6 recess\$6) same	IBM_TDB	
		plasma)) and (isolat\$9 transistor		
		interconnect\$6)		